

2SD1257, 2SD1257A

Silicon NPN epitaxial planar type

For power switching

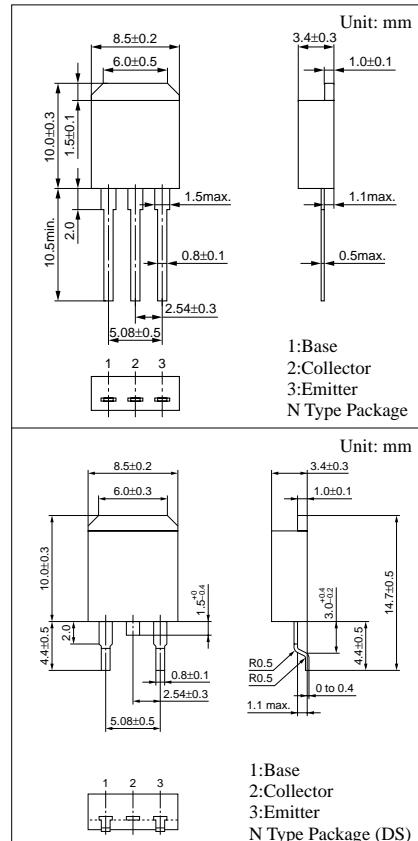
Complementary to 2SB0934 (2SB934)

■ Features

- Low collector to emitter saturation voltage $V_{CE(sat)}$
- Satisfactory linearity of forward current transfer ratio h_{FE}
- Large collector current I_C
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

■ Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	130	V
2SD1257A	2SD1257A	150	
Collector to emitter voltage	V_{CEO}	80	V
2SD1257A	2SD1257A	100	
Emitter to base voltage	V_{EBO}	7	V
Peak collector current	I_{CP}	15	A
Collector current	I_C	7	A
Collector power dissipation	P_C	40	W
$T_C=25^\circ\text{C}$	$T_a=25^\circ\text{C}$	1.3	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



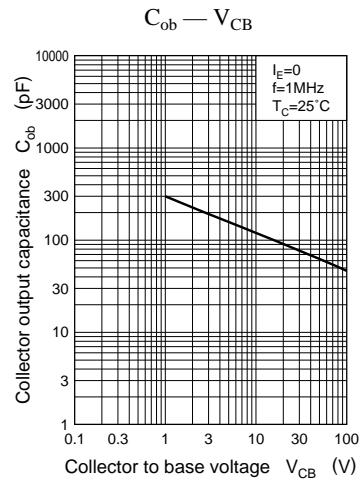
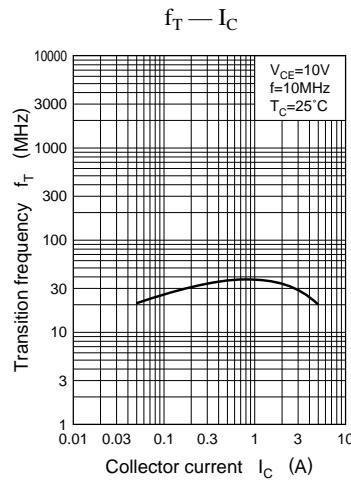
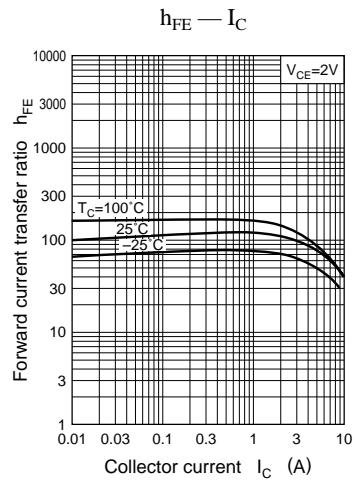
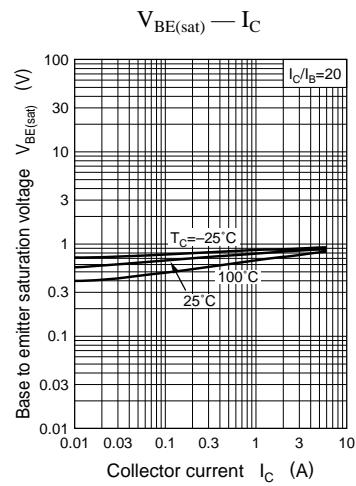
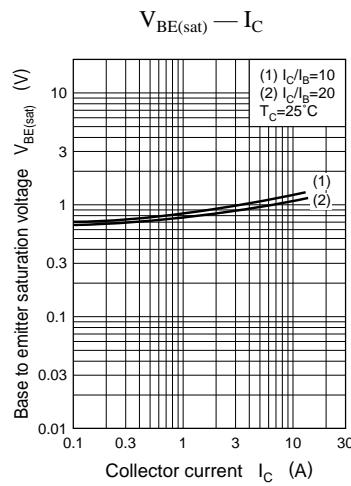
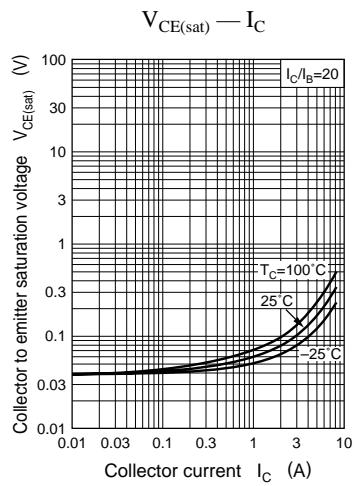
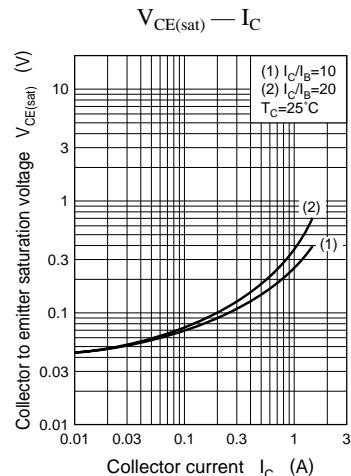
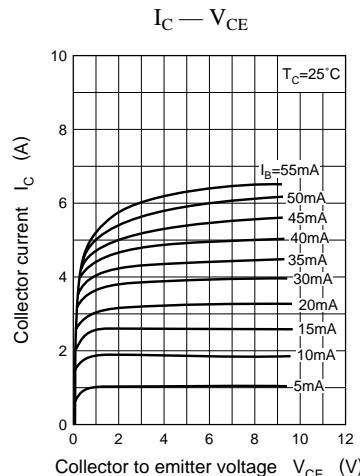
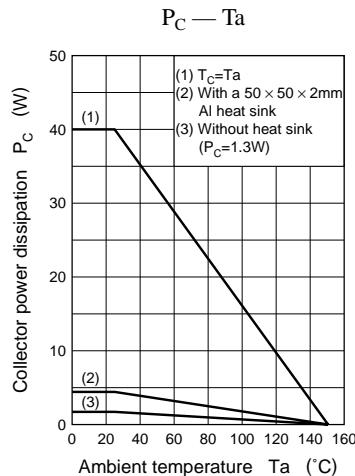
■ Electrical Characteristics ($T_C=25^\circ\text{C}$)

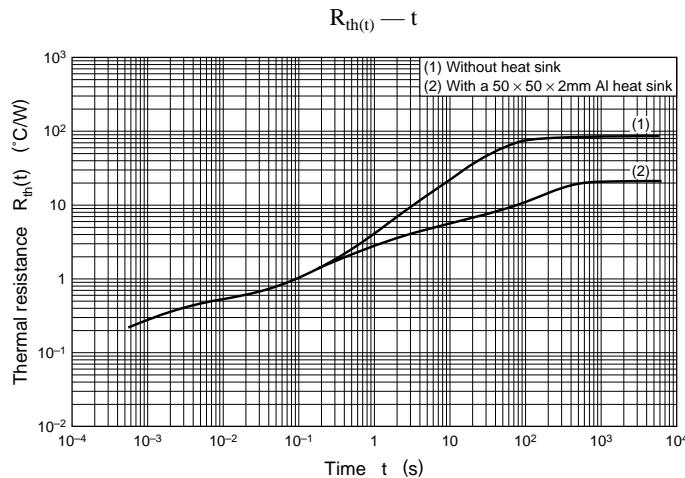
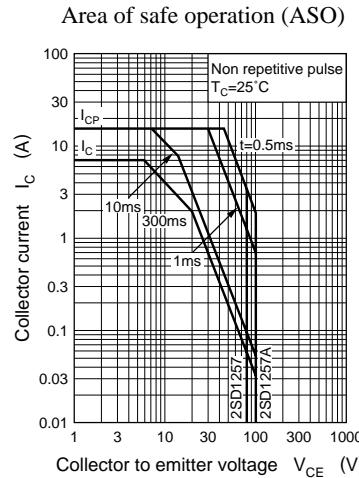
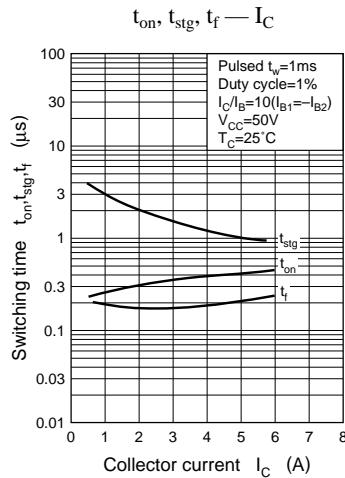
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 100\text{V}$, $I_E = 0$			10	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 5\text{V}$, $I_C = 0$			50	μA
Collector to emitter voltage	V_{CEO}	$I_C = 10\text{mA}$, $I_B = 0$	80			V
2SD1257A	2SD1257A	$I_C = 10\text{mA}$, $I_B = 0$	100			
Forward current transfer ratio	h_{FE1}	$V_{CE} = 2\text{V}$, $I_C = 0.1\text{A}$	45			
	h_{FE2}^*	$V_{CE} = 2\text{V}$, $I_C = 3\text{A}$	60		260	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 5\text{A}$, $I_B = 0.25\text{A}$			0.5	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 5\text{A}$, $I_B = 0.25\text{A}$			1.5	V
Transition frequency	f_T	$V_{CE} = 10\text{V}$, $I_C = 0.5\text{A}$, $f = 10\text{MHz}$	30			MHz
Turn-on time	t_{on}	$I_C = 3\text{A}$, $I_{B1} = 0.3\text{A}$, $I_{B2} = -0.3\text{A}$, $V_{CC} = 50\text{V}$		0.5		μs
Storage time	t_{stg}			1.5		μs
Fall time	t_f			0.1		μs

* h_{FE2} Rank classification

Rank	R	Q	P
h_{FE2}	60 to 120	90 to 180	130 to 260

Note) The part numbers in the parenthesis show conventional part number.





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